

AEC-Q100 Qualified Low Skew 1 To 4 Automotive Clock Buffer

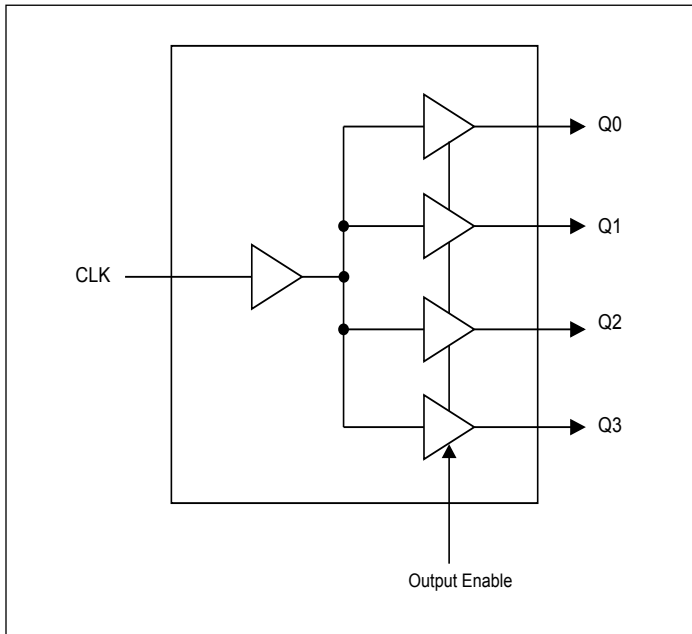
Features

- Low skew outputs (250 ps)
- Packaged in 8-pin SOIC
- Low power CMOS technology
- Operating Voltages of 1.5 V to 3.3 V
- Output Enable pin tri-states outputs
- 3.6 V tolerant input clock
- AEC-Q100 Qualified
- Automotive Grade 2 temperature range (-40 to 105 °C)
- Automotive Grade 3 temperature range (-40 to 85 °C)

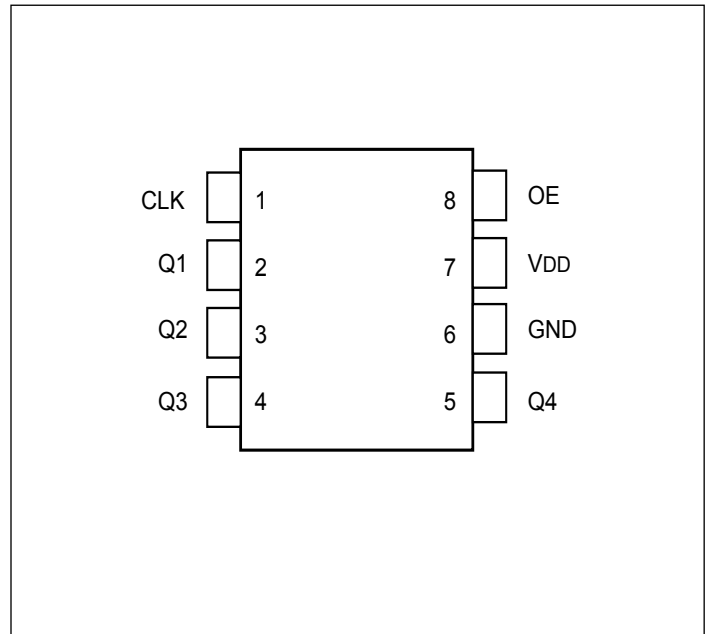
Description

The PI6C49CB04AQ is an automotive qualified low skew, single input to four output, clock buffer. Perfect for fanning out multiple clock outputs.

Block Diagram



Pin Configuratoin



Pin Descriptions

Pin#	Pin Name	Pin Type	Pin Description
1	CLK	Input	Clock Input. 3.3 V tolerant input.
2	Q1	Output	Clock Output 1.
3	Q2	Output	Clock Output 2.
4	Q3	Output	Clock Output 3.
5	Q4	Output	Clock Output 4.
6	GND	Power	Connect to ground.
7	VDD	Power	Connect to 1.5 V, 1.8V, 2.5V or 3.3V.
8	OE	Input	Output Enable. Tri-states outputs when low. Connect to VDD for normal operation.

External Components

A minimum number of external components are required for proper operation. A decoupling capacitor of 0.01 μF should be connected between VDD on pin 7 and GND on pin 6, as close to the device as possible. A 33 Ω series terminating resistor may be used on each clock output if the trace is longer than 1 inch.

Maximum Ratings

Supply Voltage, VDD	4.6V
Output Enable and All Outputs	-0.5 V to VDD+0.5 V
CLK	-0.5 V to 3.6 V (VDD > 0V)
Ambient Operating Temperature	-40 to +105 °C
Storage Temperature	-65 to +150°C
Soldering Temperature	260°C
ESD Protection (HBM)	2000 V
Junction Temperature	125°C max

Note:

Stresses above the ratings listed below can cause permanent damage to the PI6C49X0204AQ. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied.

Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

Recommended Operation Conditions

Parameter	Min.	Typ.	Max.	Units
Ambient Operating Temperature (Automotive Grade 2)	-40		+105	°C
Ambient Operating Temperature (Automotive Grade 3)	-40		+85	°C
Power Supply Voltage (measured in respect to GND)	+1.425		+3.6	V

DC ELECTRICAL CHARACTERISTICS

VDD=1.5 V ±5%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		1.425	1.5	1.575	V
V _{IH}	Input High Voltage	Note 1, CLK	0.9		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.575	V
I _{IH}	Input High Current	Note 1, CLK, OE			40	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -6 mA	0.95			V
V _{OL}	Output Low Voltage	I _{OL} = 6 mA			0.45	V
IDD	Operating Supply Current	5pF, 160 MHz		15	21	mA
		5pF, 100 MHz		13	17	mA
		5pF, 50 MHz		7	9	mA
		5pF, 25 MHz		4	5.5	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±12		mA

Notes: 1. Nominal switching threshold is VDD/2

VDD=1.8 V ±5%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		1.7	1.8	1.89	V
V _{IH}	Input High Voltage	Note 1, CLK	1.1		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.6	V
I _{IH}	Input High Current	Note 1, CLK, OE			50	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -8 mA	1.4			V
V _{OL}	Output Low Voltage	I _{OL} = 8 mA			0.4	V
IDD	Operating Supply Current	5pF, 160 MHz		22	28	mA
		5pF, 100 MHz		17	21	mA
		5pF, 50 MHz		9	12	mA
		5pF, 25 MHz		5	7	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±20		mA

Notes: 1. Nominal switching threshold is VDD/2

VDD=2.5 V ±5%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		2.375	2.5	2.625	V
V _{IH}	Input High Voltage	Note 1, CLK	1.7		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.7	V
I _{IH}	Input High Current	Note 1, CLK, OE			60	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -8 mA	2			V
V _{OL}	Output Low Voltage	I _{OL} = 8 mA			0.4	V
IDD	Operating Supply Current	5pF, 100 MHz		24	30	mA
		5pF, 50 MHz		12	15	mA
		5pF, 25 MHz		7	9	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±50		mA

Notes: 1. Nominal switching threshold is VDD/2

VDD=3.3 V ±10%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		3.0	3.3	3.6	V
V _{IH}	Input High Voltage	Note 1, CLK	2.4		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.7	V
I _{IH}	Input High Current	Note 1, CLK, OE			85	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -8 mA	2.8			V
V _{OL}	Output Low Voltage	I _{OL} = 8 mA			0.2	V
IDD	Operating Supply Current	5pF, 100 MHz		32	38	mA
		5pF, 50 MHz		16	19	mA
		5pF, 25 MHz		10	12	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±50		mA

Notes: 1. Nominal switching threshold is VDD/2

AC ELECTRICAL CHARACTERISTICS

VDD=1.5 V ±5%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F _{OUT}	Output Frequency		0		160	MHz
t _{OR}	Output Rise Time	20% to 80%		1.0	1.5	ns
t _{OF}	Output Fall Time	20% to 80%		1.0	1.5	ns
T _{PD}	Propagation Delay (Note1)		2	3	5	ns
T _{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps

VDD=1.8 V ±5%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F _{OUT}	Output Frequency		0		160	MHz
t _{OR}	Output Rise Time	20% to 80%		1.0	1.5	ns
t _{OF}	Output Fall Time	20% to 80%		1.0	1.5	ns
T _{PD}	Propagation Delay (Note1)		1.3	2	4	ns
T _{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps
J _{ADD}	Additive Jitter	@156.25MHz, 12k to 20MHz		0.1		ps

PI6C49CB04AQ

VDD=2.5 V ±5%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F _{OUT}	Output Frequency		0		160	MHz
t _{OR}	Output Rise Time	20% TO 80%		1.0	1.5	ns
t _{OF}	Output Fall Time	20% TO 80%		1.0	1.5	ns
T _{PD}	Propagation Delay (Note1)		0.8	1.5	3	ns
T _{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps
J _{ADD}	Additive Jitter	@156.25MHz, 12k to 20MHz		0.05		ps

Notes:

1. With rail to rail input clock
2. Between any 2 outputs with equal loading.

VDD=3.3 V ±10%, Ambient temperature -40 to +105° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F _{OUT}	Output Frequency		0		100	MHz
t _{OR}	Output Rise Time	20% TO 80%		1.0	1.5	ns
t _{OF}	Output Fall Time	20% TO 80%		1.0	1.5	ns
T _{PD}	Propagation Delay (Note1)		0.8	1.0	2.5	ns
T _{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps
J _{ADD}	Additive Jitter	@156.25MHz, 12k to 20MHz		0.05		ps

Notes:

1. With rail to rail input clock
2. Between any 2 outputs with equal loading.

DC ELECTRICAL CHARACTERISTICS

VDD=1.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		1.425	1.5	1.575	V
V _{IH}	Input High Voltage	Note 1, CLK	0.9		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.575	V
I _{IH}	Input High Current	Note 1, CLK, OE			40	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -6 mA	0.95			V
V _{OL}	Output Low Voltage	I _{OL} = 6 mA			0.45	V
IDD	Operating Supply Current	5pF, 160 MHz		15	21	mA
		5pF, 100 MHz		13	17	mA
		5pF, 50 MHz		7	9	mA
		5pF, 25 MHz		4	5.5	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±12		mA

Notes: 1. Nominal switching threshold is VDD/2

VDD=1.8 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		1.7	1.8	1.89	V
V _{IH}	Input High Voltage	Note 1, CLK	1.1		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.6	V
I _{IH}	Input High Current	Note 1, CLK, OE			50	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -8 mA	1.4			V
V _{OL}	Output Low Voltage	I _{OL} = 8 mA			0.4	V
IDD	Operating Supply Current	5pF, 160 MHz		22	28	mA
		5pF, 100 MHz		17	21	mA
		5pF, 50 MHz		9	12	mA
		5pF, 25 MHz		5	7	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±20		mA

Notes: 1. Nominal switching threshold is VDD/2

VDD=2.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		2.375	2.5	2.625	V
V _{IH}	Input High Voltage	Note 1, CLK	1.7		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.7	V
I _{IH}	Input High Current	Note 1, CLK, OE			60	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -8 mA	2			V
V _{OL}	Output Low Voltage	I _{OL} = 8 mA			0.4	V
IDD	Operating Supply Current	5pF, 200 MHz		46	56	mA
		5pF, 100 MHz		24	30	mA
		5pF, 50 MHz		12	15	mA
		5pF, 25 MHz		7	9	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±50		mA

Notes: 1. Nominal switching threshold is VDD/2

VDD=3.3 V ±10%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Operating Voltage		3.0	3.3	3.6	V
V _{IH}	Input High Voltage	Note 1, CLK	2.4		3.6	V
V _{IL}	Input Low Voltage	Note 1, CLK			0.7	V
I _{IH}	Input High Current	Note 1, CLK, OE			85	μA
I _{IL}	Input Low Current	Note 1, CLK, OE			1	μA
V _{OH}	Output High Voltage	I _{OH} = -8 mA	2.8			V
V _{OL}	Output Low Voltage	I _{OL} = 8 mA			0.2	V
IDD	Operating Supply Current	5pF, 200 MHz		62	75	mA
		5pF, 100 MHz		32	38	mA
		5pF, 50 MHz		16	19	mA
		5pF, 25 MHz		10	12	mA
Z _O	Nominal Output Impedance			20		Ω
C _{IN}	Input Capacitance	CLK, OE pin		5		pF
I _{OS}	Short Circuit Current			±50		mA

Notes: 1. Nominal switching threshold is VDD/2

AC ELECTRICAL CHARACTERISTICS

VDD=1.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F_{OUT}	Output Frequency		0		166	MHz
tOR	Output Rise Time	20% to 80%		1.0	1.5	ns
tOF	Output Fall Time	20% to 80%		1.0	1.5	ns
T_{PD}	Propagation Delay (Note1)		2	3	5	ns
T_{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps

VDD=1.8 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F_{OUT}	Output Frequency		0		166	MHz
tOR	Output Rise Time	20% to 80%		1.0	1.5	ns
tOF	Output Fall Time	20% to 80%		1.0	1.5	ns
T_{PD}	Propagation Delay (Note1)		1.3	2	4	ns
T_{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps
J_{ADD}	Additive Jitter	@156.25MHz, 12k to 20MHz		0.1		ps

VDD=2.5 V ±5%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F_{OUT}	Output Frequency		0		200	MHz
tOR	Output Rise Time	20% TO 80%		1.0	1.5	ns
tOF	Output Fall Time	20% TO 80%		1.0	1.5	ns
T_{PD}	Propagation Delay (Note1)		0.8	1.5	3	ns
T_{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps
J_{ADD}	Additive Jitter	@156.25MHz, 12k to 20MHz		0.05		ps

Notes:

1. With rail to rail input clock
2. Between any 2 outputs with equal loading.

PI6C49CB04AQ

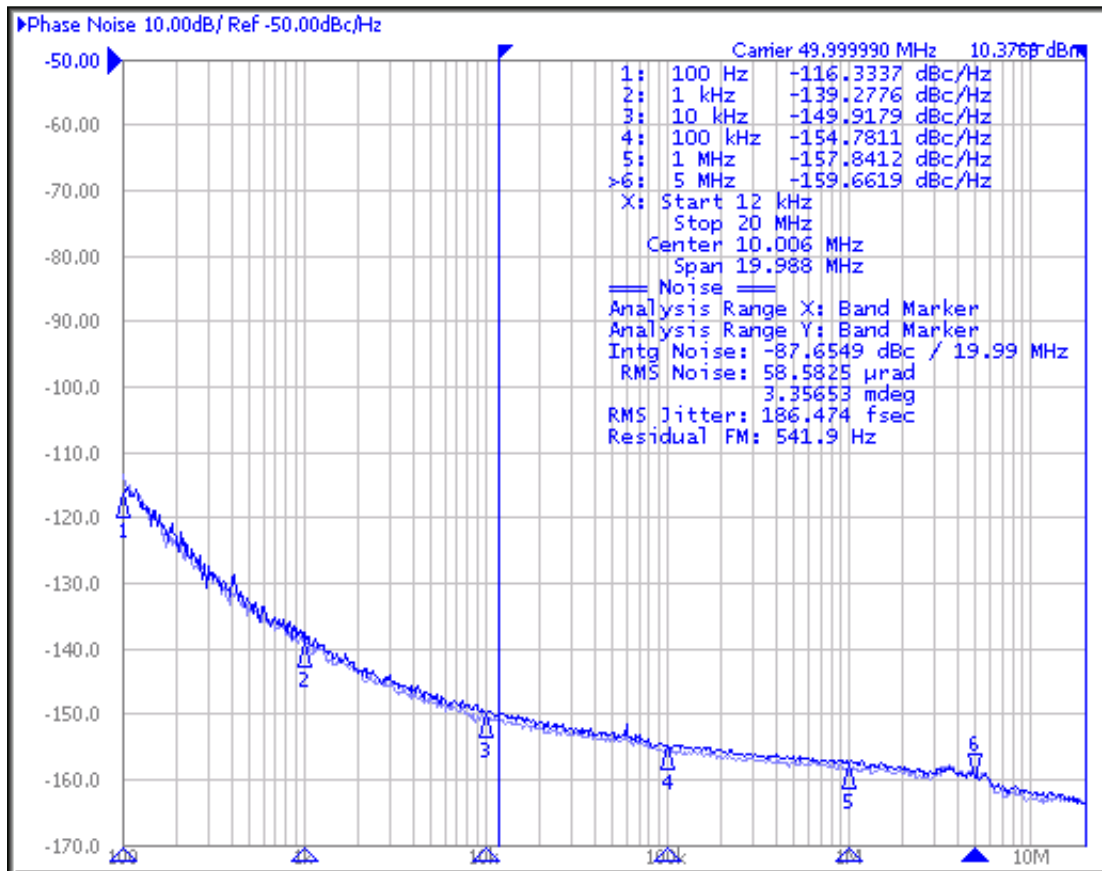
VDD=3.3 V ±10%, Ambient temperature -40 to +85° C, unless stated otherwise

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
F_{OUT}	Output Frequency		0		200	MHz
tOR	Output Rise Time	20% TO 80%		1.0	1.5	ns
tOF	Output Fall Time	20% TO 80%		1.0	1.5	ns
T_{PD}	Propagation Delay (Note1)		0.8	1.0	2.5	ns
T_{SK}	Output to Output Skew (Note2)	Rising edges at VDD/2		0	±250	ps
J_{ADD}	Additive Jitter	@156.25MHz, 12k to 20MHz		0.05		ps

Notes:

1. With rail to rail input clock
2. Between any 2 outputs with equal loading.

Phase Noise Plot



THERMAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
θ_{JA}	Thermal Resistance Junction to Ambient	Still air		157		°C/W
θ_{JC}	Thermal Resistance Junction to Case			42		°C/W

Application information

Suggest for Unused Inputs and Outputs

LVC MOS Input Control Pins

It is suggested to add pull-up=4.7k and pull-down=1k for LVC MOS pins even though they have internal pull-up/down but with much higher value (>=50k) for higher design reliability.

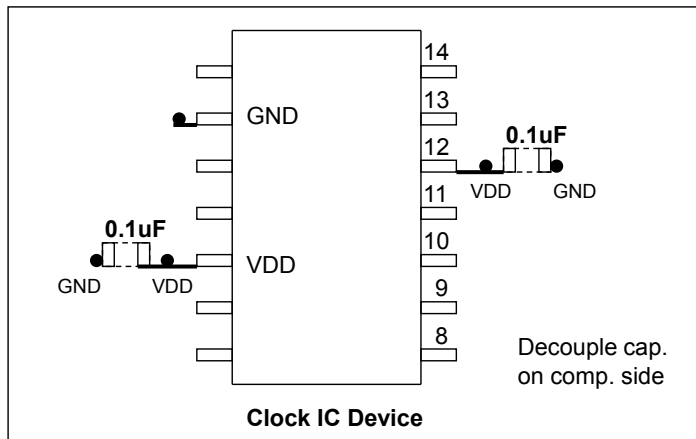
Outputs

All unused outputs are suggested to be left open and not connected to any trace. This can lower the IC power consumption.

Power Decoupling & Routing

VDD Pin Decoupling

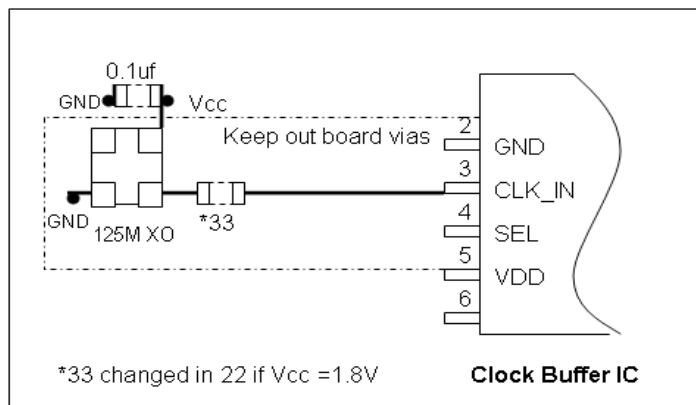
Each VDD pin must have a 0.1uF decoupling capacitor. For better decoupling, 1uF can be used. Locating the decoupling capacitor on the component side has better decoupling filter result as shown.



Placement of Decoupling caps

CMOS Clock Trace Routing

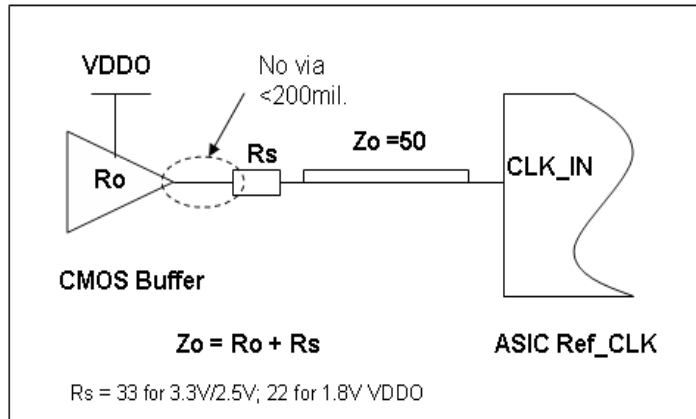
Please ensure that there is a sufficient keep-out area to the adjacent trace (>20mil.). In an example using a 125MHz XO driving a buffer IC, it is better to route the clock trace on the component side with a 33 ohm termination resistor.



CMOS Output Termination

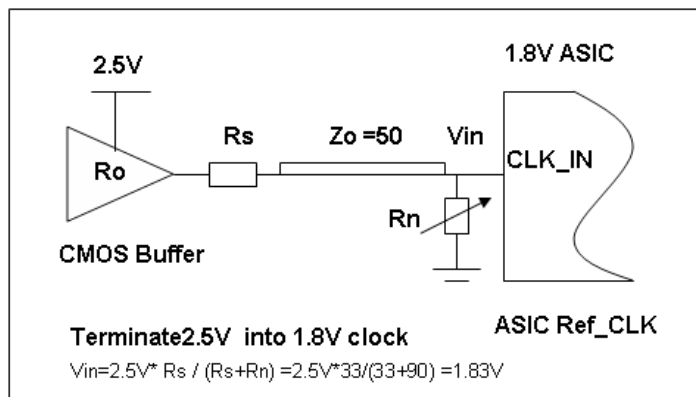
Popular CMOS Output Termination

The most popular CMOS termination is a serial resistor close to the output pin (<=200mil). It is simple and balances the drive strength. The resistor's value can be fine tuned for best performance during board bring-up based on VDDO voltage used.



Combining Serial and Parallel Termination

Designers can also use a parallel termination for CMOS outputs. For example, a 50 ohm pull-down resistor can be used at the Rx side to reduce signal reflection, but it reduces the signals V_{swing} in half. This pull-down can be combined with a serial resistor to form a smaller clock voltage difference. The following diagram shows how to transition a 2.5V clock into 1.8V clock.



$R_s = 33$ ohm with $R_n = 100$ ohm, to transition 3.3V CMOS to 2.5V

$R_s = 43$ ohm with $R_n = 70$ ohm to transition 3.3V CMOS to 1.8V

Clock Jitter Definitions

Total jitter= RJ + DJ

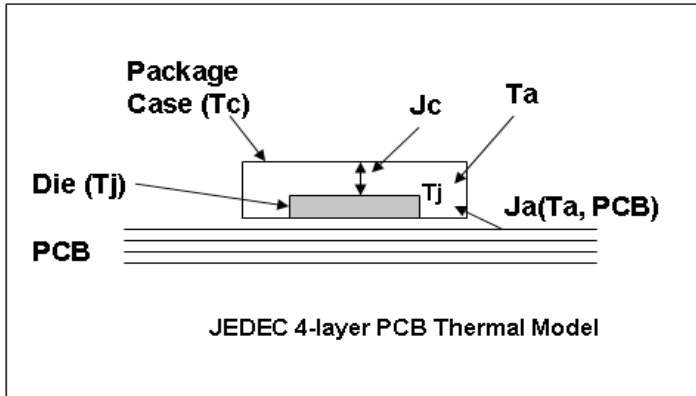
Random Jitter (RJ) is unpredictable and unbounded timing noise that can fit in a Gaussian math distribution in RMS. RJ test values are directly related with how long or how many test samples are available. Deterministic Jitter (DJ) is timing jitter that is predictable and periodic in fixed interference frequency. Total Jitter (TJ) is the combination of random jitter and deterministic jitter: , where is a factor based on total test sample count. JEDEC std. specifies digital clock TJ in 10k random samples.

Phase Jitter

Phase noise is short-term random noise attached on the clock carrier and it is a function of the clock offset from the carrier, for example dBc/Hz@10kHz which is phase noise power in 1-Hz normalized bandwidth vs. the carrier power @10kHz offset. Integration of phase noise in plot over a given frequency band yields RMS phase jitter, for example, to specify phase jitter <=1ps at 12k to 20MHz offset band as SONET standard specification.

Device Thermal Calculation

The JEDEC thermal model in a 4-layer PCB is shown below.



JEDEC IC Thermal Model

Important factors to influence device operating temperature are:

- 1) The power dissipation from the chip (P_{chip}) is after subtracting power dissipation from external loads. Generally it can be the no-load device I_{dd}
- 2) Package type and PCB stack-up structure, for example, 1oz 4 layer board. PCB with more layers and are thicker has better heat dissipation
- 3) Chassis air flow and cooling mechanism. More air flow M/s and adding heat sink on device can reduce device final die junction temperature T_j

The individual device thermal calculation formula:

$$T_j = T_a + P_{chip} \times J_a$$

$$T_c = T_j - P_{chip} \times J_c$$

J_a ___ Package thermal resistance from die to the ambient air in C/W unit; This data is provided in JEDEC model simulation. An air flow of 1m/s will reduce J_a (still air) by 20~30%

J_c ___ Package thermal resistance from die to the package case in C/W unit

T_j ___ Die junction temperature in C (industry limit <125C max.)

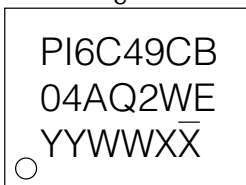
T_a ___ Ambient air temperature in C

T_c ___ Package case temperature in C

P_{chip} ___ IC actually consumes power through I_{ee}/GND current

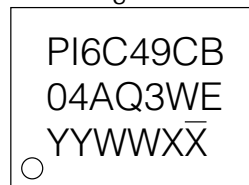
Part Marking

Q Package-2



Y: Year
W: Workweek
1st X: Assembly Code
2nd X: Fab Code

Q Package-3



Y: Year
W: Workweek
1st X: Assembly Code
2nd X: Fab Code

Packaging Mechanical: 8-SOIC (W)

SYMBOLS	MIN.	NOM.	MAX.
A	—	—	1.75
A1	0.10	—	0.25
A2	1.25	—	—
b	0.31	—	0.51
c	0.10	—	0.25
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.27 BSC		
L	0.40	—	1.27
h	0.25	—	0.50
θ°	0	—	8

UNIT : mm

NOTE :
 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES
 2. DIMENSIONS EXCLUDE BURRS, MOLD FLASH OR PROTRUSIONS
 3. REFER JEDEC MS-012

		DATE: 02/21/14
DESCRIPTION: 8-Pin, 150mil-Wide, SOIC		
PACKAGE CODE: W (W8)		
DOCUMENT CONTROL #: PD-1001	REVISION: G	

15-0103

For latest package info.

please check: <http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/>

Ordering Information⁽¹⁻³⁾

Ordering Code	Package Code	Package Description	Operating Temperature
PI6C49CB04AQ2WEX	W	8-pin, 150mil-Wide (SOIC)	-40 to 105 °C
PI6C49CB04AQ3WEX	W	8-pin, 150mil-Wide (SOIC)	-40 to 85 °C

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See <http://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/
3. E = Pb-free and Green
4. X suffix = Tape/Reel

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and definitive format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated

www.diodes.com

单击下面可查看定价，库存，交付和生命周期等信息

[>>Diodes Incorporated\(达达科技\(美台\)\)](#)